

isc Silicon NPN Power Transistor

2N3583

DESCRIPTION

- Contunuous Collector Current- $I_C=1A$
- Power Dissipation- $P_D=35W$ @ $T_C=25^{\circ}C$
- Collector-Emitter Saturation Voltage-
: $V_{CE(sat)}=5.0V(Max)$ @ $I_C=1A$

APPLICATIONS

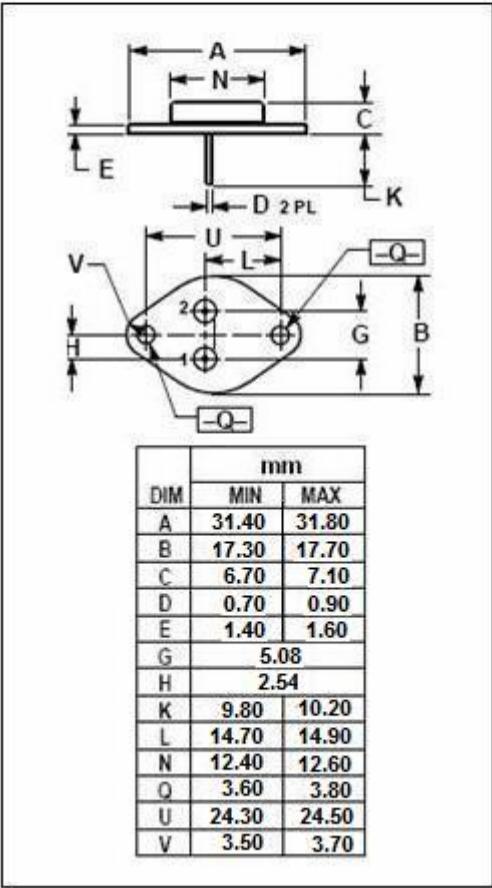
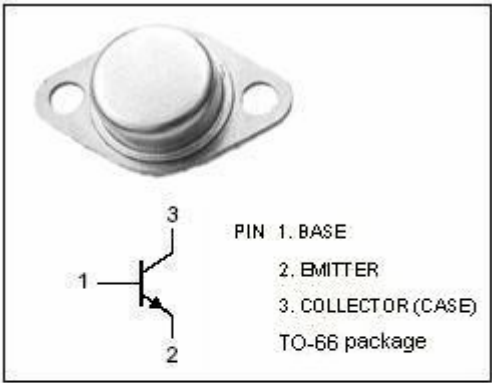
- Designed for high-speed switching and linear amplifier appli-
cation for high-voltage operational amplifiers, switching regu-
lators, converters,deflection stages and high fidelity amplifiers.

ABSOLUTE MAXIMUM RATINGS($T_a=25^{\circ}C$)

SYMBOL	PARAMETER	VALUE	UNIT
V_{CBO}	Collector-Base Voltage	250	V
V_{CEO}	Collector-Emitter Voltage	175	V
V_{EBO}	Emitter-Base Voltage	6	V
I_C	Collector Current-Continuous	1.0	A
I_{CM}	Collector Current-Peak	5.0	A
I_B	Base Current	1.0	A
P_C	Collector Power Dissipation@ $T_C=25^{\circ}C$	35	W
T_J	Junction Temperature	200	$^{\circ}C$
T_{stg}	Storage Temperature	-65~200	$^{\circ}C$

THERMAL CHARACTERISTICS

SYMBOL	PARAMETER	MAX	UNIT
$R_{th\ j-c}$	Thermal Resistance,Junction to Case	5.0	$^{\circ}C/W$



ISC Silicon NPN Power Transistor**2N3583****ELECTRICAL CHARACTERISTICS** **$T_C=25^{\circ}\text{C}$ unless otherwise specified**

SYMBOL	PARAMETER	CONDITIONS	MIN	MAX	UNIT
$V_{CEO(SUS)}$	Collector-Emitter Sustaining Voltage	$I_C = 200\text{mA}$; $I_B = 0$	175		V
$V_{CE(sat)}$	Collector-Emitter Saturation Voltage	$I_C = 1\text{A}$; $I_B = 0.125\text{A}$		5.0	V
$V_{BE(on)}$	Base-Emitter On Voltage	$I_C = 1\text{A}$; $V_{CE} = 10\text{V}$		1.4	V
I_{CEO}	Collector Cutoff Current	$V_{CE} = 150\text{V}$; $I_B = 0$		10	mA
I_{CEX}	Collector Cutoff Current	$V_{CE} = 225\text{V}$; $V_{BE(off)} = 1.5\text{V}$ $V_{CE} = 225\text{V}$; $V_{BE(off)} = 1.5\text{V}$, $T_C = 150^{\circ}\text{C}$		1.0 3.0	mA
I_{EBO}	Emitter Cutoff Current	$V_{EB} = 6\text{V}$; $I_C = 0$		5.0	mA
h_{FE-1}	DC Current Gain	$I_C = 0.1\text{A}$; $V_{CE} = 10\text{V}$	40		
h_{FE-2}	DC Current Gain	$I_C = 0.5\text{A}$; $V_{CE} = 10\text{V}$	40	200	
h_{FE-3}	DC Current Gain	$I_C = 1\text{A}$; $V_{CE} = 10\text{V}$	10		